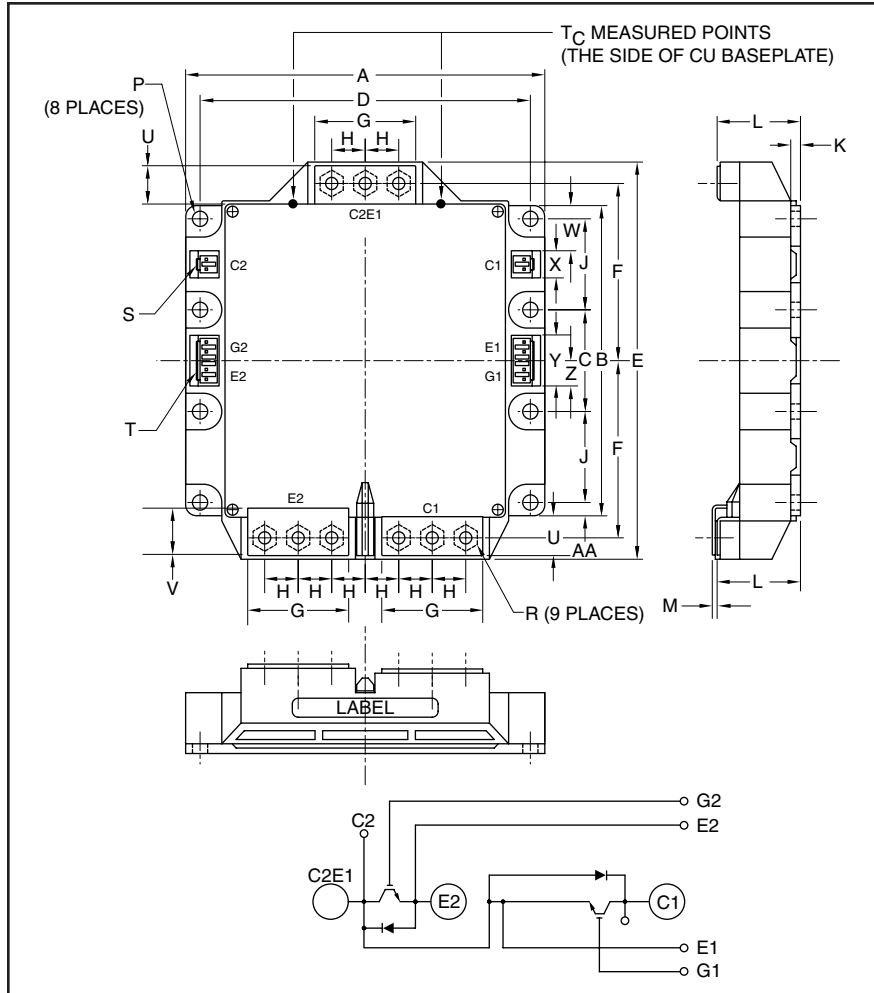


Mega Power Dual™ IGBTMOD 900 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	5.91	150.0
B	5.10	129.5
C	1.67±0.01	42.5±0.25
D	5.41±0.01	137.5±0.25
E	6.54	166.0
F	2.91±0.01	74.0±0.25
G	1.65	42.0
H	0.55	14.0
J	1.50±0.01	38.0±0.25
K	0.16	4.0

Housing Type (J.S.T. MFG. CO. LTD)

S = VHR-2N

T = VHR-5N

Dimensions	Inches	Millimeters
L	1.36 +0.04/-0.02	34.6 +1.0/-0.5
M	0.075±0.08	1.9±0.2
P	0.26	6.5
R	M6 Metric	M6
U	0.62	15.7
V	0.71	18.0
W	0.75	19.0
X	0.43	11.0
Y	0.83	21.0
Z	0.41	10.5
AA	0.22	5.5



Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:

- ☐ High Power UPS
- ☐ Large Motor Drives
- ☐ Utility Interface Inverters

Ordering Information:

Example: Select the complete module number you desire from the table - i.e. CM900DU-24NF is a 1200V (V_{CES}), 900 Ampere Dual IGBTMOD Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	900	24

CM900DU-24NF

Mega Power Dual™ IGBTMOD

900 Amperes/1200 Volts

Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	CM900DU-24NF	Units
Junction Temperature	T_j	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	1200	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	± 20	Volts
Collector Current DC ($T_C = 96^\circ\text{C}$)**	I_C	900	Amperes
Peak Collector Current ($T_j \leq 150^\circ\text{C}$)	I_{CM}	1800*	Amperes
Emitter Current***	I_E	900	Amperes
Peak Emitter Current***	I_{EM}	1800*	Amperes
Maximum Collector Dissipation ($T_j < 150^\circ\text{C}$) ($T_C = 25^\circ\text{C}$)	P_C	2550	Watts
Mounting Torque, M6 Mounting Screws	–	40	in-lb
Mounting Torque, M6 Main Terminal Screw	–	40	in-lb
Weight (Typical)	–	1400	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{iso}	2500	Volts

Static Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$	–	–	1	mA
Gate Leakage Current	I_{GES}	$V_{GE} = V_{GES}, V_{CE} = 0V$	–	–	1.0	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 90\text{mA}, V_{CE} = 10V$	6	7	8	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 900A, V_{GE} = 15V, T_j = 25^\circ\text{C}$	–	1.8	2.5	Volts
(Without Lead Resistance)	(Chip)	$I_C = 900A, V_{GE} = 15V, T_j = 125^\circ\text{C}$	–	2.0	–	Volts
Module Lead Resistance	$R_{(lead)}$	$I_C = 900A$, Terminal-chip	–	0.143	–	$\text{m}\Omega$
Total Gate Charge	Q_G	$V_{CC} = 600V, I_C = 900A, V_{GE} = 15V$	–	4800	–	nC
Emitter-Collector Voltage***	V_{EC}	$I_E = 900A, V_{GE} = 0V$	–	–	3.2	Volts

Dynamic Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics		Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0V$	–	–	140	nF
Output Capacitance		C_{oes}		–	–	16	nF
Reverse Transfer Capacitance		C_{res}		–	–	3	nF
Inductive	Turn-on Delay Time	$t_{d(on)}$	$V_{CC} = 600V,$	–	–	600	ns
Load	Rise Time	t_r	$I_C = 900A, I_E = 900A,$	–	–	200	ns
Switch	Turn-off Delay Time	$t_{d(off)}$	$V_{GE1} = V_{GE2} = 15V,$	–	–	800	ns
Times	Fall Time	t_f	$R_G = 0.35\Omega,$	–	–	300	ns
Diode Reverse Recovery Time***		t_{rr}	Inductive Load	–	–	500	ns
Diode Reverse Recovery Charge***		Q_{rr}	Switching Operation	–	50	–	μC

* Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

** T_C measurement points is just under the chips. If this value is used, $R_{th(f-a)}$ should be measured just under the chips.

***Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

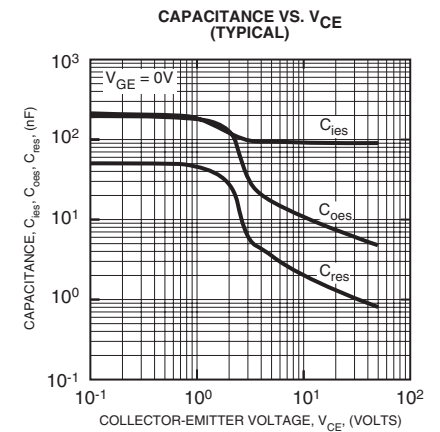
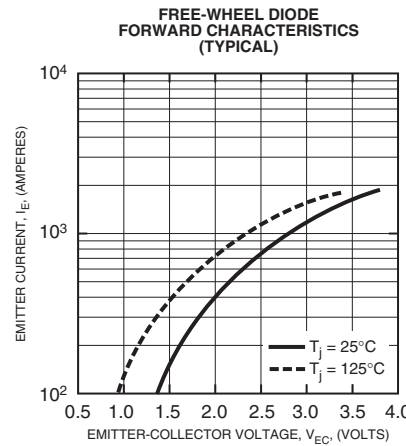
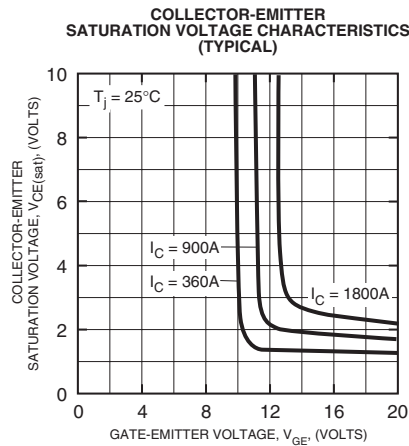
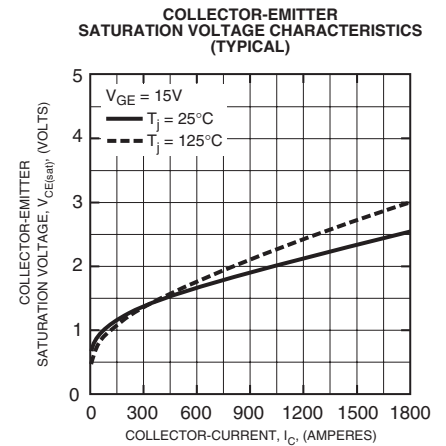
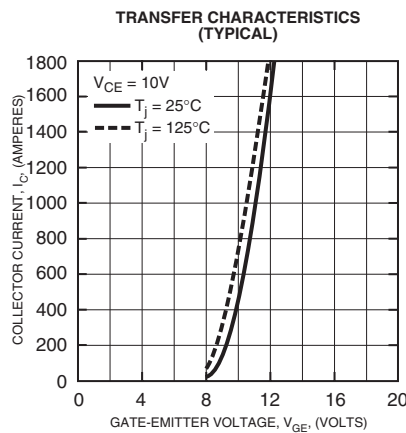
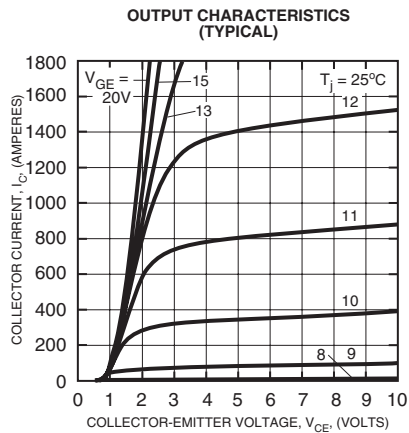
CM900DU-24NF

Mega Power Dual™ IGBTMOD

900 Amperes/1200 Volts

Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)Q}$	Per IGBT 1/2 Module, T_C Reference Point per Outline Drawing	—	—	0.049	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)D}$	Per FWDi 1/2 Module, T_C Reference Point per Outline Drawing	—	—	0.078	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c')Q}$	Per IGBT 1/2 Module, T_C Reference Point Under Chip	—	—	0.021	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c')D}$	Per FWDi 1/2 Module, T_C Reference Point Under Chip	—	—	0.034	$^\circ\text{C/W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per 1/2 Module, Thermal Grease Applied	—	0.016	—	$^\circ\text{C/W}$
External Gate Resistance	R_G		0.35	—	2.2	Ω

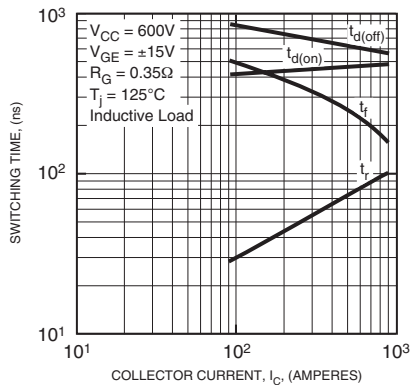


CM900DU-24NF

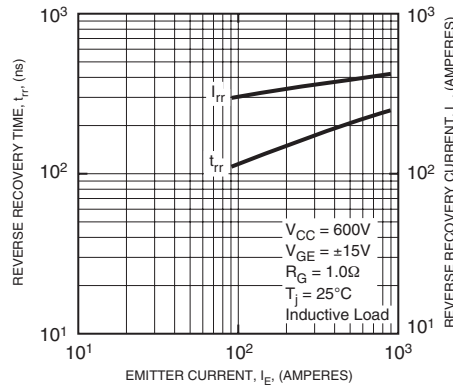
Mega Power Dual™ IGBTMOD

900 Amperes/1200 Volts

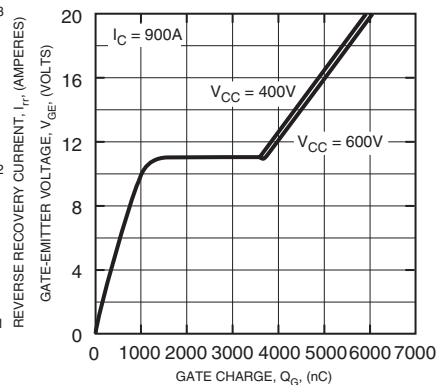
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)



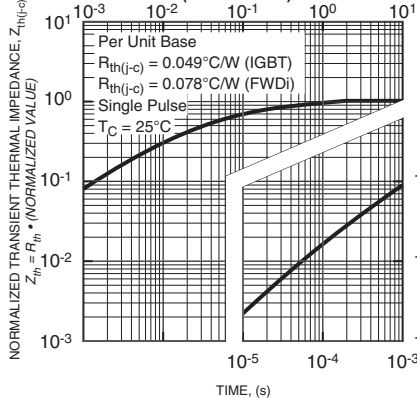
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)



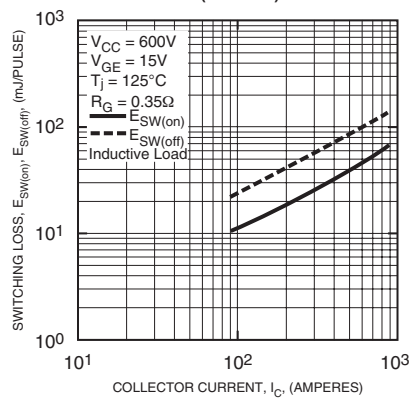
GATE CHARGE, V_{GE}



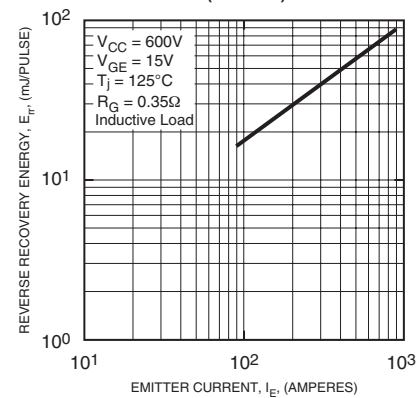
TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(IGBT & FWDI)



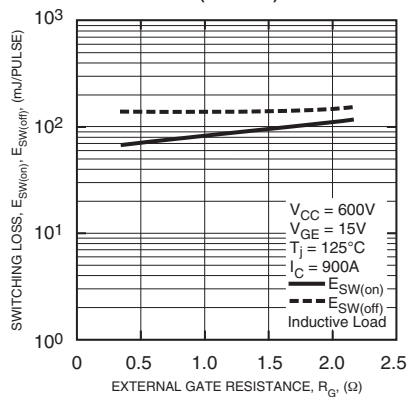
SWITCHING LOSS VS. COLLECTOR CURRENT
(TYPICAL)



REVERSE RECOVERY ENERGY VS.
EMITTER CURRENT
(TYPICAL)



SWITCHING ENERGY VS.
EXTERNAL GATE RESISTANCE
(TYPICAL)



REVERSE RECOVERY ENERGY VS.
EXTERNAL GATE RESISTANCE
(TYPICAL)

